

**Amendments to the Specification:**

A. Please amend the title to:

--METHOD OF OPERATING A SEMICONDUCTOR MEMORY ARRAY OF  
FLOATING GATE MEMORY CELLS WITH BURIED BIT-LINE AND  
VERTICAL WORD LINE TRANSISTOR--

B. Please add to the first line of the specification the following priority claim information:

--This application is a divisional of U.S. Application No. 09/982,413, filed October 17,  
2001.--